

MMBT4401WT1

Preferred Device

Switching Transistor

NPN Silicon

Features

- Moisture Sensitivity Level: 1
- ESD Rating: Human Body Model; 4 kV,
Machine Model; 400 V
- Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current - Continuous	I_C	600	mAdc

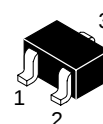
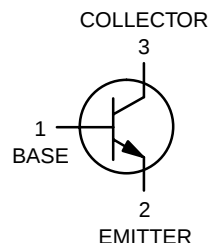
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board $T_A = 25^\circ\text{C}$	P_D	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$



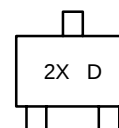
ON Semiconductor®

<http://onsemi.com>



SC-70 (SOT-323)
CASE 419
STYLE 3

MARKING DIAGRAM



2X = Specific Device Code
D = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
MMBT4401WT1	SC-70	3000/Tape & Reel
MMBT4401WT1G	SC-70 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (Note 1) ($I_C = 1.0\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	40	–	Vdc
Collector–Base Breakdown Voltage ($I_C = 0.1\text{ mAdc}$, $I_E = 0$)	$V_{(BR)CBO}$	60	–	Vdc
Emitter–Base Breakdown Voltage ($I_E = 0.1\text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	6.0	–	Vdc
Base Cutoff Current ($V_{CE} = 35\text{ Vdc}$, $V_{EB} = 0.4\text{ Vdc}$)	I_{BEV}	–	0.1	μAdc

ON CHARACTERISTICS (Note 1)

DC Current Gain ($I_C = 0.1\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 150\text{ mAdc}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 500\text{ mAdc}$, $V_{CE} = 2.0\text{ Vdc}$)	h_{FE}	20 40 80 100 40	– – – 300 –	–
Collector–Emitter Saturation Voltage ($I_C = 150\text{ mAdc}$, $I_B = 15\text{ mAdc}$) ($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$)	$V_{CE(sat)}$	– –	0.4 0.75	Vdc
Base–Emitter Saturation Voltage ($I_C = 150\text{ mAdc}$, $I_B = 15\text{ mAdc}$) ($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$)	$V_{BE(sat)}$	0.75 –	0.95 1.2	Vdc
Collector Cutoff Current ($V_{CE} = 35\text{ Vdc}$, $V_{EB} = 0.4\text{ Vdc}$)	I_{CEX}	–	0.1	μAdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ($I_C = 20\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	250	–	MHz
Collector–Base Capacitance ($V_{CB} = 5.0\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{cb}	–	6.5	pF
Emitter–Base Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{eb}	–	30	pF
Input Impedance ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{ie}	1.0	15	k Ω
Voltage Feedback Ratio ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{re}	0.1	8.0	$\times 10^{-4}$
Small–Signal Current Gain ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	40	500	–
Output Admittance ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{oe}	1.0	30	μmhos

SWITCHING CHARACTERISTICS

Delay Time	$(V_{CC} = 30\text{ Vdc}$, $V_{EB} = 2.0\text{ Vdc}$, $I_C = 150\text{ mAdc}$, $I_{B1} = 15\text{ mAdc}$)	t_d	–	15	ns
Rise Time		t_r	–	20	
Storage Time	$(V_{CC} = 30\text{ Vdc}$, $I_C = 150\text{ mAdc}$, $I_{B1} = I_{B2} = 15\text{ mAdc}$)	t_s	–	225	ns
Fall Time		t_f	–	30	

1. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

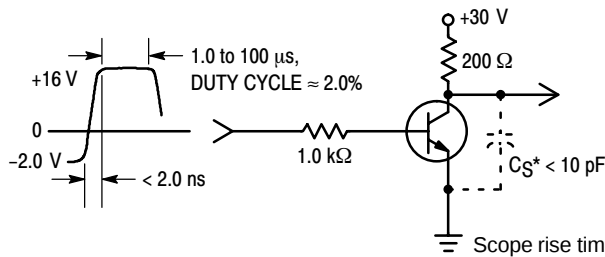


Figure 1. Turn–On Time

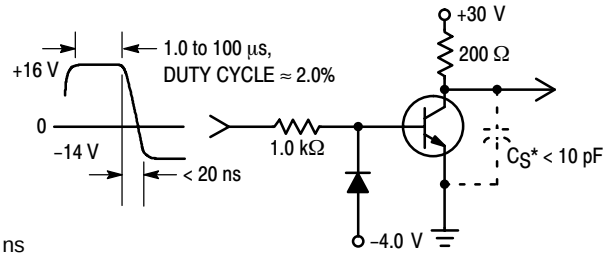


Figure 2. Turn–Off Time

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TRANSIENT CHARACTERISTICS

— 25°C — 100°C

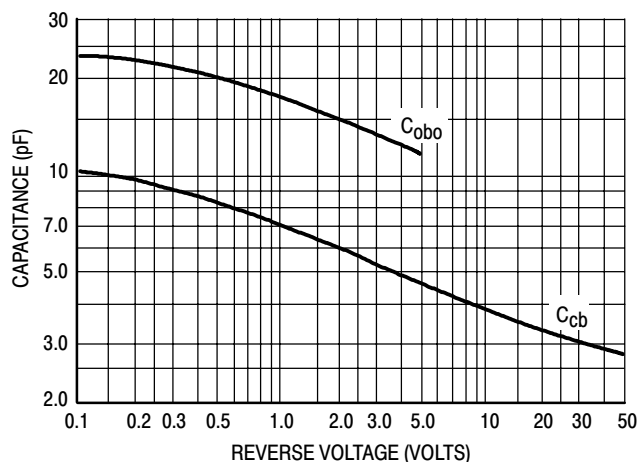


Figure 3. Capacitances

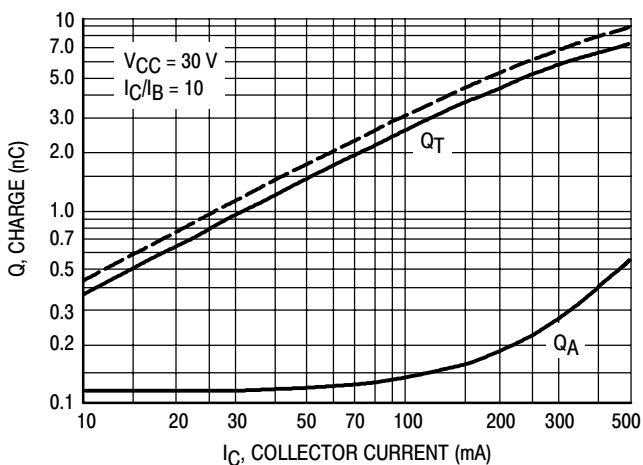


Figure 4. Charge Data

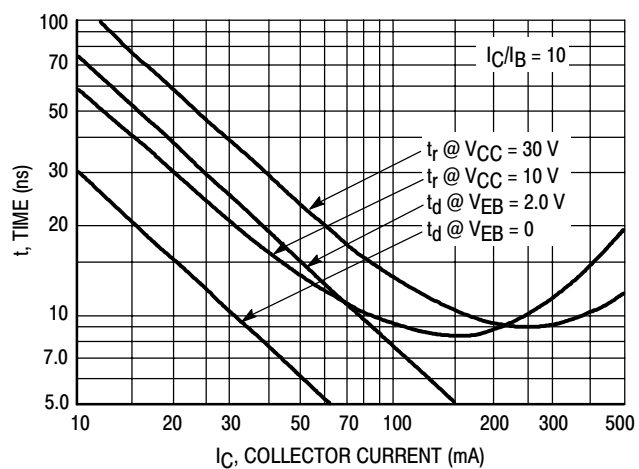


Figure 5. Turn-On Time

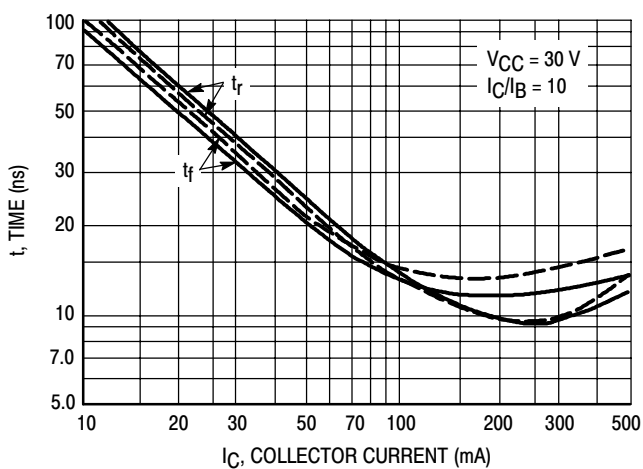


Figure 6. Rise and Fall Times

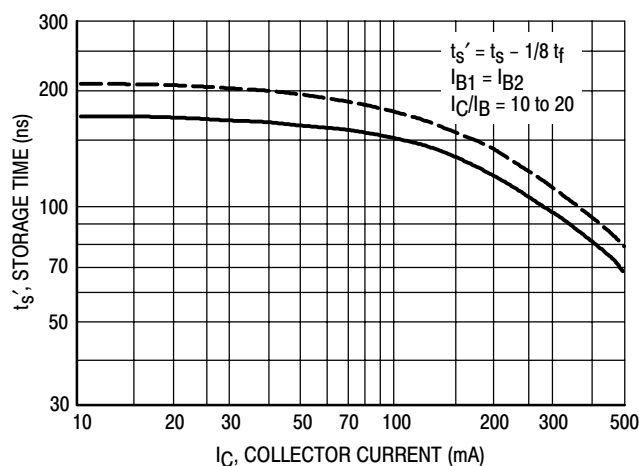


Figure 7. Storage Time

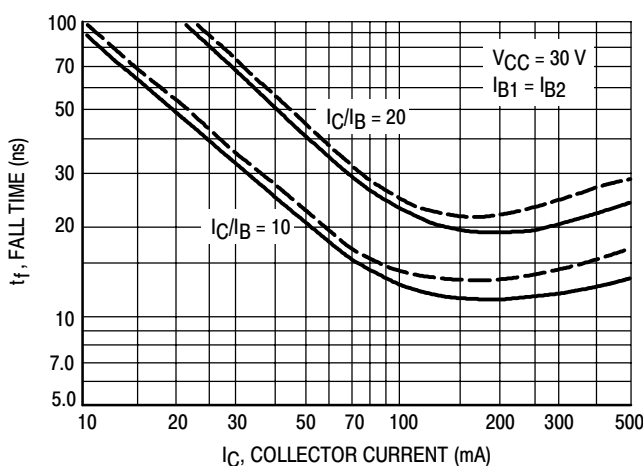


Figure 8. Fall Time

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SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

$V_{CE} = 10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$; Bandwidth = 1.0 Hz

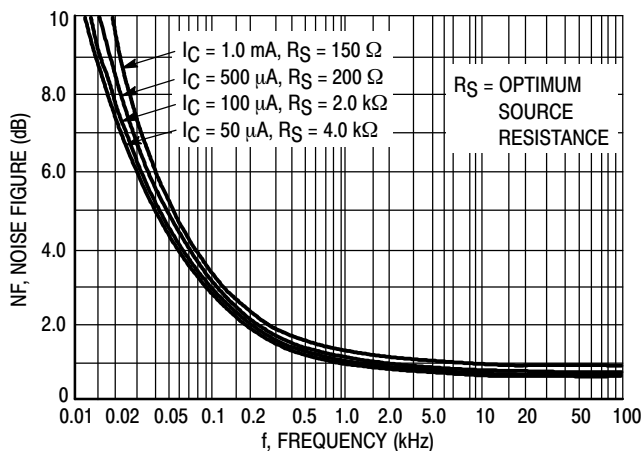


Figure 9. Frequency Effects

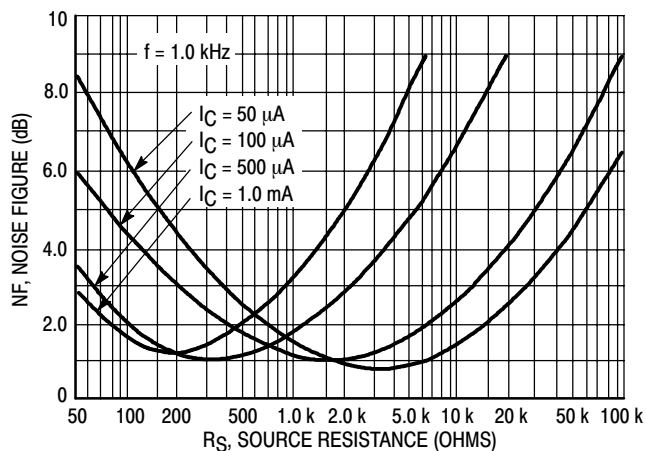


Figure 10. Source Resistance Effects

h PARAMETERS

$V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$, $T_A = 25^\circ\text{C}$

This group of graphs illustrates the relationship between h_{fe} and other “h” parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were selected from the MMBT4401WT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

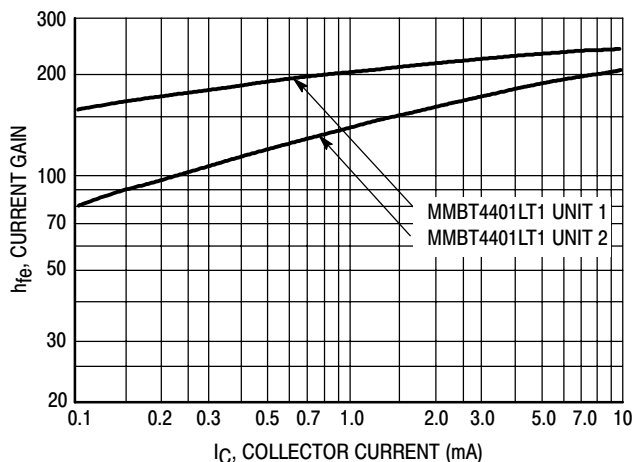


Figure 11. Current Gain

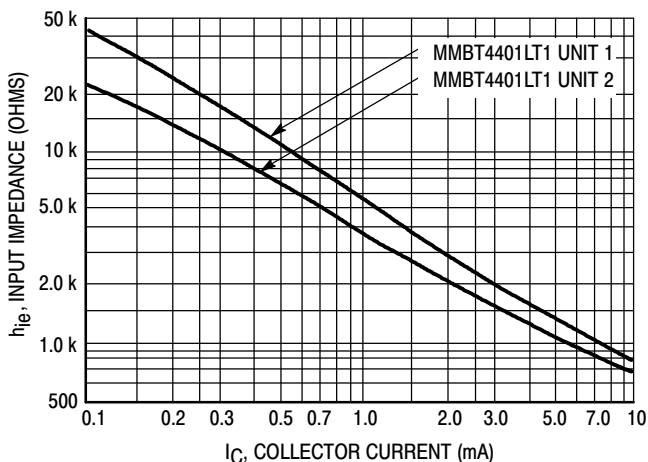


Figure 12. Input Impedance

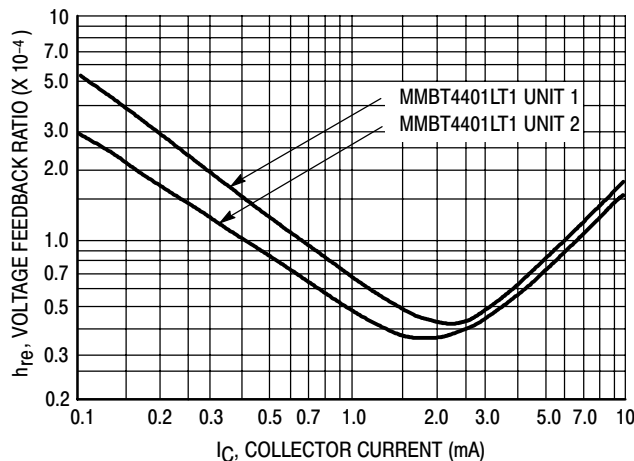


Figure 13. Voltage Feedback Ratio

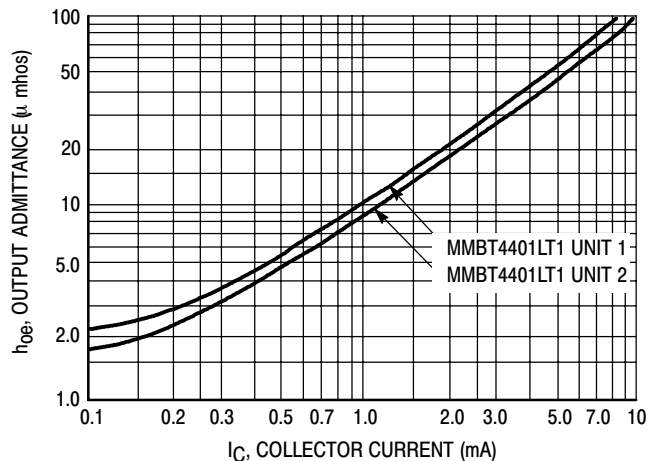


Figure 14. Output Admittance

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STATIC CHARACTERISTICS

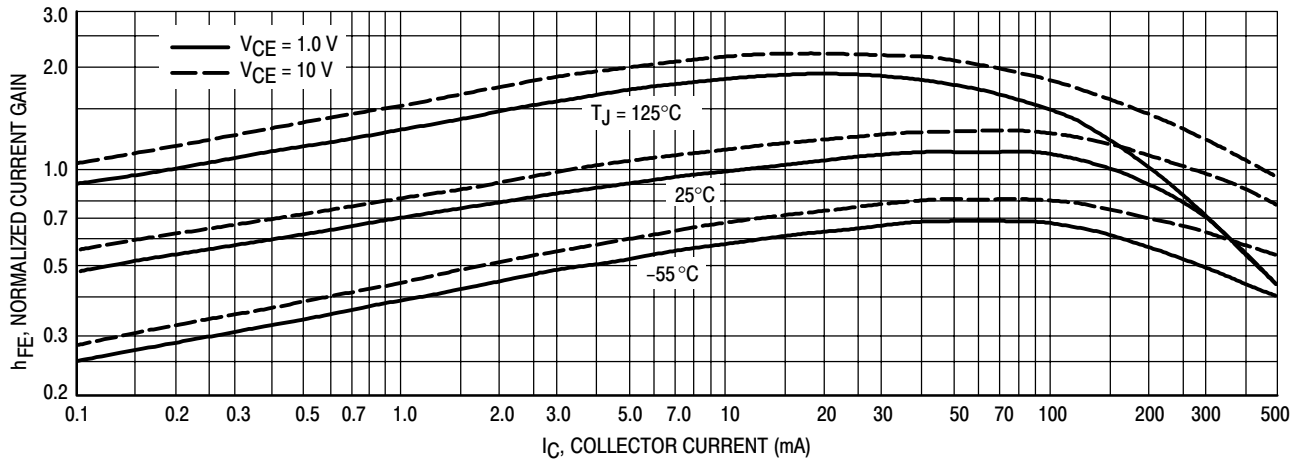


Figure 15. DC Current Gain

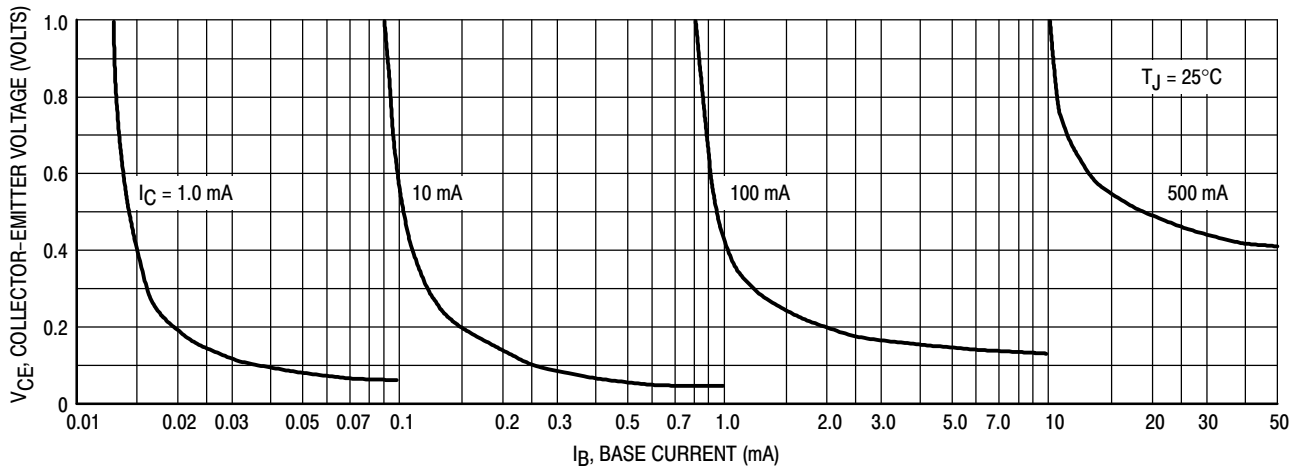


Figure 16. Collector Saturation Region

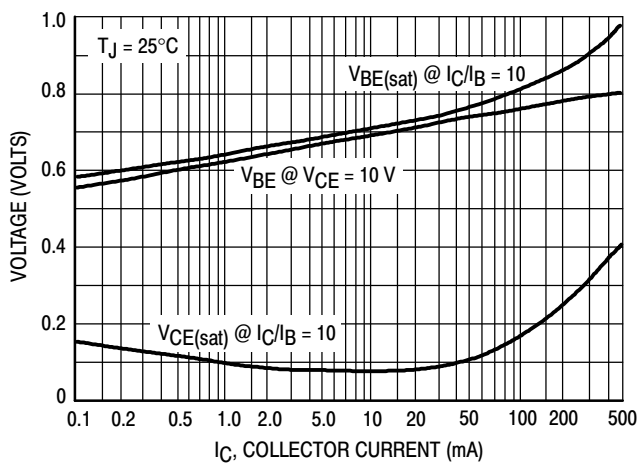


Figure 17. "On" Voltages

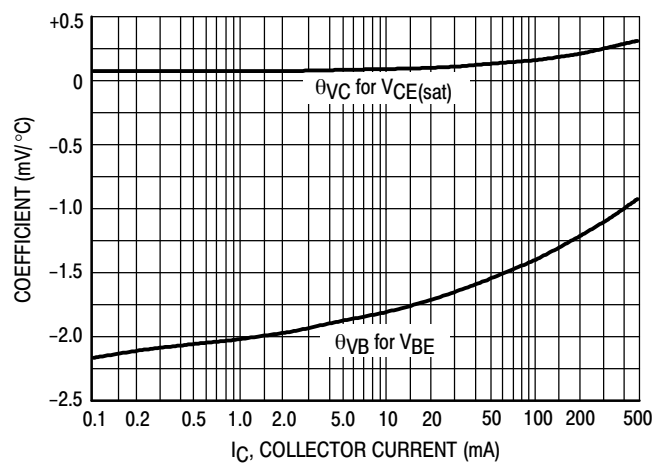


Figure 18. Temperature Coefficients